

DSK12~DSK110

Major Ratings and Characteristics

$I_{F(AV)}$	1.0 A
V_{RRM}	20 V to 100 V
I_{FSM}	25 A
V_F	0.55 V , 0.70 V, 0.85V
$T_j \text{ max.}$	125 C

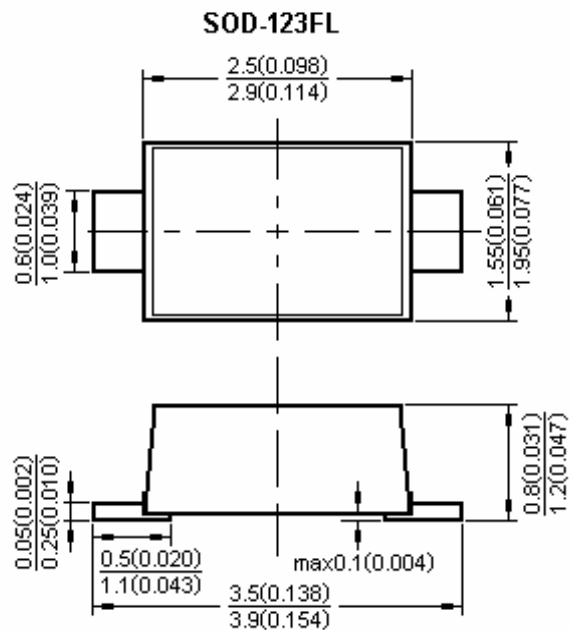


Features

- Low profile package
- Ideal for automated placement
- Ultrafast reverse recovery time
- Low power losses, high efficiency
- Low forward voltage drop
- High surge capability
- High temperature soldering:
• 260°C/10 seconds at terminals
- Component in accordance to
RoHS 2002/95/1 and WEEE 2002/96/EC

Mechanical Data

- **Case:** JEDEC SOD-123FL molded plastic body over passivated chip
- **Terminals:** Solder plated, solderable per J-STD-002B and JESD22-B102D
- **Polarity:** Laser band denotes cathode end



Dimensions in millimeters and (inches)

Maximum Ratings & Thermal Characteristics & Electrical Characteristics

($T_A = 25\text{ }^\circ\text{C}$ unless otherwise noted)

	Symbol	DSK12	DSK13	DSK14	DSK15	DSK16	DSK18	DSK110	UNIT
Maximum repetitive peak reverse voltage	V_{RRM}	20	30	40	50	60	80	100	V
Maximum RMS voltage	V_{RMS}	14	21	28	35	42	56	70	V
Maximum DC blocking voltage	V_{DC}	20	30	40	50	60	80	100	V
Maximum average forward rectified current	$I_{F(AV)}$	1							A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load	I_{FSM}	25							A
Maximum instantaneous forward voltage at 1.0A	V_F	0.55		0.70		0.85		V	
Maximum DC reverse current $T_A = 25\text{ }^\circ\text{C}$ at Rated DC blocking voltage $T_A = 100\text{ }^\circ\text{C}$	I_R	1.0 10							mA
Typical junction capacitance at 4.0 V , 1MHz	C_J	110							
Operating junction and storage temperature range	T_J, T_{STG}	- 65 to +125							$^\circ\text{C}$

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Characteristic Curves ($T_A=25^\circ\text{C}$ unless otherwise noted)

Fig.1 Forward Current Derating Curve

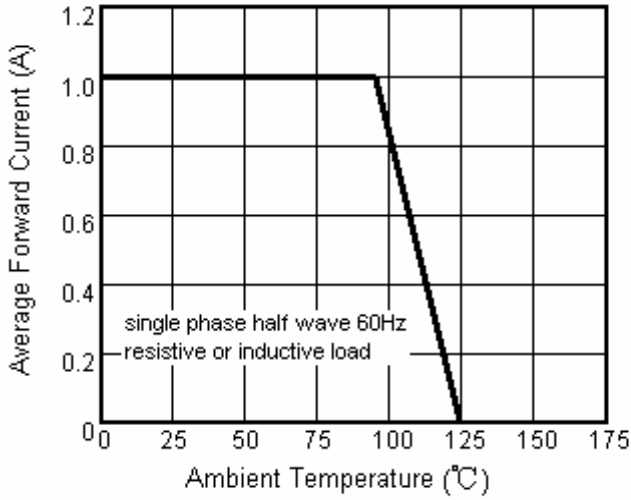


Fig.2 Maximum Non-Repetitive Peak Forward Surge Current

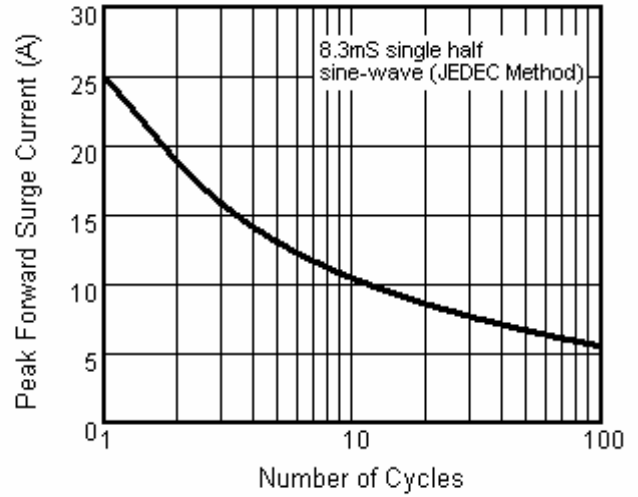


Fig.3 Typical Instantaneous Forward Characteristics

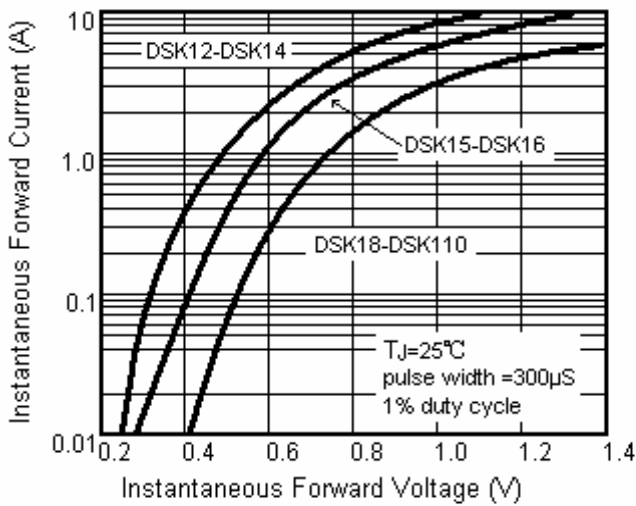


Fig.4 Typical Reverse Characteristics

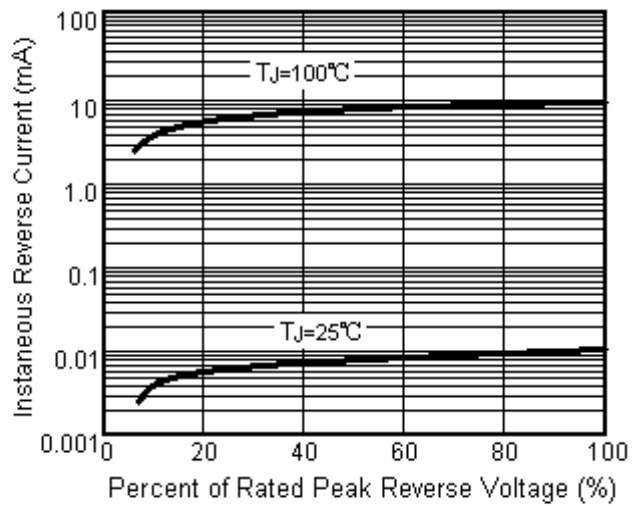


Fig.5 Typical Junction Capacitance

